# MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet



**SOT - 23** 



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

## TRANSISTOR (PNP)

### **FEATURE**

- Collector-Base Voltage
- Complement to C945-MS

MARKING: CS

## MAXIMUM RATINGS(Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-150	mA
Pc	Collector Power Dissipation	200	mW
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

# ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -5uA,I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1mA , I <sub>B</sub> =0	-50			٧
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -50uA, I <sub>C</sub> =0	-5			٧
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -60 V , I <sub>E</sub> =0			-0.1	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5 V , I <sub>C</sub> =0			-0.1	uA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -6 V, I <sub>C</sub> = -1mA	120		475	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -100mA, I <sub>B</sub> =- 10mA		-0.18	-0.3	٧
Base-emitter voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> =-6V,I <sub>C</sub> =-1.0mA	-0.58	-0.62	-0.68	V
Transition frequency	f⊤	V <sub>CE</sub> =-6V,I <sub>C</sub> =-10mA	50			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V,I <sub>E</sub> =0,f=1MH <sub>Z</sub>		4.5	7	pF
Noise figure	NF	$V_{CE}$ =-6V, $I_{C}$ =-0.3mA, Rg=10k $\Omega$ ,f=100H <sub>Z</sub>		6	20	dB

# **CLASSIFICATION OF h**<sub>FE</sub>

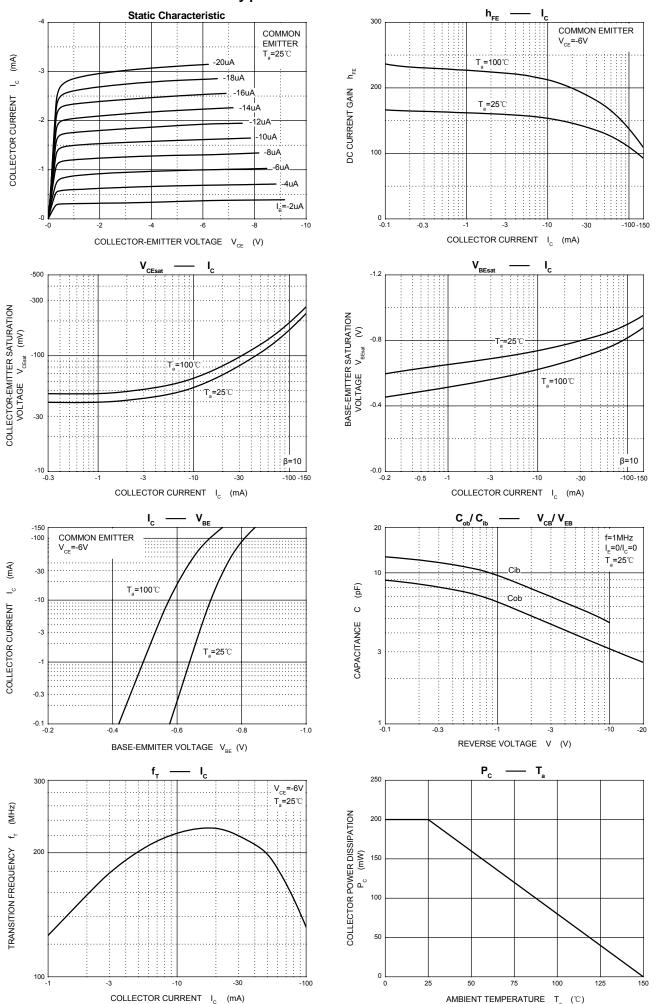
Rank	L	Н		
Range	120-200	200-400		



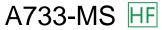
Semiconductor

### Compiance

# **Typical Characterisitics**



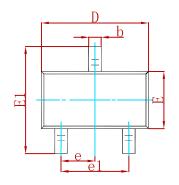


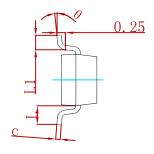


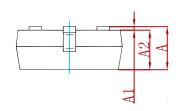


#### Semiconductor Compiance

# **PACKAGE MECHANICAL DATA**

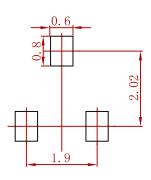






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	) TYP	0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

# **REEL SPECIFICATION**

P/N	PKG	QTY
A733-MS	SOT-23	3000



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